



BN15(2CN4,BZU15)

GLASS PASSIVATED SILICON BOOST DIODE

Features:

1. Silicon diffusion mesa.
2. Glass Passivated package.
3. Small volume, light weight.
4. Small high-temperature leakage.
5. Good thermal stability.
6. High reliability.
7. Implementation of standards: QZJ840611



TECHNICAL DATA:

($T_a = 25^\circ\text{C}$)

Parameter name	Symbols	Unit	Specifications	Test Condition
Use for	High-frequency, ultra-high-frequency, voltage boost circuit.			
Store temperature	T	$^\circ\text{C}$	-55~+150	
Quality Class	GS			
Peak Repetitive Reverse Voltage	V_{RRM}	V	50~1400	
Average Forward Current	$I_{F(AV)}$	A	1.5	
Peak Forward Voltage	V_{FM}	V	1.6	$I = AI_{F(AV)}, A = 3.1415926$
Average Forward Voltage	V_F	V	A~C:0.65, D:0.8,E:1.0	$I = I_{F(AV)}$
Non-repeat Forward Surge Current	I_{FSM}	A	30	Single-phase industrial frequency sine half wave 10ms
Peak Reverse Current	I_{RM1}	μA	10	$V_R = V_{RRM}, T_a = 25^\circ\text{C}$
Peak Reverse Current	I_{RM2}	μA	200	$V_R = V_{RRM}, T_a = 125^\circ\text{C}$
Junction Temperature	T_{jm}	$^\circ\text{C}$	150	
Reverse Recovery Time	t_{rr}	μS	1	$V_R = 10\text{V}, I_F = 50\text{mA}, R_L = 75\text{ohms}$

SPECIFICATIONS:

A	B	C	D	E
50V	100V	200V	300V	400V

Outline and Dimensions: